



ED (21) 2041  
(Revision – 2021)

**A23-2106220059A**

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Reg. No.....

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**DIPLOMA EXAMINATION IN ENGINEERING/TECHNOLOGY/  
MANAGEMENT/COMMERCIAL PRACTICE, APRIL – 2023**

**BASIC ELECTRONICS**

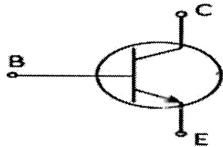
[Maximum Marks: 75]

[Time: 3 Hours]

**PART-A**

**I. Answer *all* the following questions in one word or one sentence. Each question carries 'one' mark.**

**(9 x 1 = 9 Marks)**

		Module Outcome	Cognitive level
1.	Define doping.	M1.01	R
2.	Draw the V-I characteristics of PN junction diode.	M1.03	R
3.	List the modes of operation of transistor.	M2.02	R
4.	State the relationship between $\alpha$ and $\beta$ .	M2.03	R
5.	 Identify the component.	M2.01	R
6.	Draw the equivalent circuit of UJT.	M3.01	R
7.	Define intrinsic standoff ratio.	M3.02	R
8.	List any two non-linear wave shaping circuits.	M4.04	R
9.	Name the output waveform obtained, when a square wave is given as input to the integrator circuit.	M4.03	R

**PART-B**

**II. Answer any *eight* questions from the following. Each question carries 'three' marks.**

**(8 x 3 = 24 Marks)**

		Module Outcome	Cognitive level
1.	List and define any three specifications of diode.	M1.04	R
2.	Explain the drift current and diffusion current of diode.	M1.02	U
3.	“CE configuration is most widely used in amplifier circuits”. Justify the statement.	M2.04	U
4.	Explain the basic conditions that must be satisfied for the faithful amplification.	M2.05	U
5.	a) Classify the voltage that should be applied for the operations of N channel JFET. (2 marks) b) Interpret the operation of N channel JFET when no voltage is applied. (1 mark)	M3.02	U
6.	Draw the energy band diagram of semiconductors.	M1.01	R
7.	Define static and dynamic forward resistances of PN junction diode.	M1.03	R



8.	What are the values of TUF, ripple factor and DC output voltage having a peak voltage of 10V in a half wave rectifier circuit.	M4.01	R
9.	Explain the effect of temperature in leakage current.	M2.03	U
10.	Explain the biasing conditions for various modes of operation of transistor.	M2.02	U

**PART-C**

**Answer all questions. Each question carries 'seven' marks**

**(6 x 7 = 42 Marks)**

		Module Outcome	Cognitive level
III.	Compare P-type and N-type semiconductors. <b>OR</b>	M1.01	U
IV.	Classify and explain various biasing conditions of p-n junction.	M1.03	U
V.	Compare the three transistor configurations. <b>OR</b>	M2.04	U
VI.	Describe the physical structure of BJT with diagram.	M2.01	U
VII.	Describe the physical structure of MOSFET with diagram. <b>OR</b>	M3.01	U
VIII.	With neat sketch explain the ON state of UJT.	M3.02	U
IX.	Design and illustrate the operation of an RC integrator with square wave signal. <b>OR</b>	M4.03	A
X.	Construct and explain the operation of double slicer at +2V and -2V. Sketch the input –output waveforms. (Assume ideal diode conditions).	M4.04	A
XI.	With diagram explain the working of series inductor filter. <b>OR</b>	M4.02	U
XII.	Explain the working of half wave voltage doubler with diagram.	M4.05	U
XIII.	Draw and describe the structure of UJT. <b>OR</b>	M3.01	U
XIV.	A) Draw the symbol for N channel JFET. (2 marks) B) Draw the drain and transfer characteristics of JFET. (5 marks)	M3.01 M3.03	R R

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